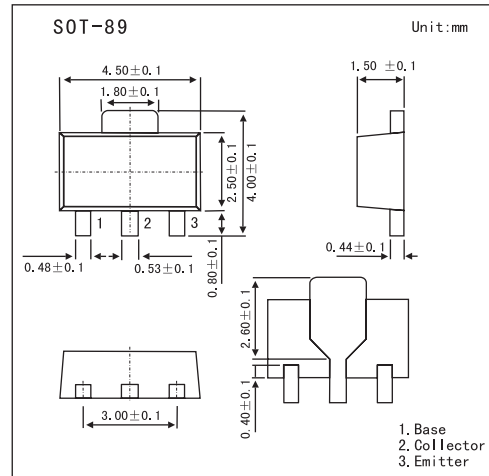


NPN Silicon Epitaxial Transistor

2SD1006



■ Features

- High collector to emitter voltage: $V_{CE0} > 100V$.

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	100	V
Collector-emitter voltage	V_{CE0}	100	V
Emitter-base voltage	V_{EB0}	5	V
Collector current	I_C	0.7	A
Collector current (pulse) *	$I_{C(pu)}$	1.2	A
Collector I power dissipation	P_C	2	W
Junction temperature	T_j	150	$^\circ C$
Storage temperature	T_{stg}	-55 to +150	$^\circ C$

*. $PW \leq 10ms$, duty cycle $\leq 50\%$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Base-emitter voltage *	V_{BE}	$V_{CE} = 10V, I_C = 10mA$	550	620	650	mV
Collector cutoff current	I_{CB0}	$V_{CB} = 100V, I_E = 0$			100	nA
Emitter cutoff current	I_{EB0}	$V_{EB} = 5V, I_C = 0$			100	nA
DC current gain *	h_{FE}	$V_{CE} = 1V, I_C = 5.0mA$	45	200		
		$V_{CE} = 1V, I_C = 100mA$	90	200	400	
Collector-emitter saturation voltage *	$V_{CE(sat)}$	$I_C = 500mA, I_B = 50mA$		0.3	0.6	V
Base-emitter saturation voltage *	$V_{BE(sat)}$	$I_C = 500mA, I_B = 50mA$		0.9	1.5	V
Output capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0, f = 1.0MHz$		10		pF
Transition product	f_T	$V_{CE} = 10V, I_E = -10mA$		90		MHz

*. $PW \leq 350\mu s$, duty cycle $\leq 2\%$

■ hFE Classification

Marking	HM	HL	HK
hFE	90~180	135~270	200~400